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Eğitim Bilgileri

Doktora, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), Türkiye 1986 - 1994

Yüksek Lisans, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Türkiye 1983 - 1985

Lisans, Fırat Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1978 - 1982

Yaptığı Tezler

Doktora, Al-siox-psi aygıtların ve güneş pillerinin elektriksel karakteristikleri, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), 1993

Yüksek Lisans, Çok ince yapı teorisi, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1950

Araştırma Alanları

Yarıiletken ve Süperiletken Malzemeler, Optik Özellikler, Kompozitler, Nanomalzemeler, Yoğun Madde 1:Yapısal, Mekanik ve Termal Özellikler, Yoğun Madde 2:Elektronik Yapı, Elektrik, Manyetik ve Optik Özellikler

Akademik Unvanlar / Görevler

Prof. Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik, 2011 - Devam Ediyor

Doç. Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik, 2005 - 2011

Yrd. Doç. Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik, 1994 - 2005

Araştırma Görevlisi, Gazi Üniversitesi, Fen Fakültesi, Fizik, 1983 - 1994

Yönetilen Tezler

ALTINDAL Ş., Photovoltaic and temperature Characteristics of the designed Schottky barrier diodes (SBDs) as a function of temperature and illumination, Doktora, H.MELOUD(Öğrenci), 2021

ALTINDAL Ş., Au/(nanografite-PVP)/n-Si (MPS) yapıların hazırlanması ve elektrik ile dielektrik özelliklerinin geniş bir frekans ve voltaj aralığında incelenmesi, Doktora, A.MUHAMMED(Öğrenci), 2021

Altındal Ş., Dielektrik çok katmanlı geniş bantlı kızılötesi metamalzeme soğurucunun tasarımı, üretimi ve karakterizasyonu, Doktora, B.AKIN(Öğrenci), 2021

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin frekans ve voltaja bağlı incelenmesi, Doktora, Ö.SEVGİLİ(Öğrenci), 2020

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) SCHOTTKY ENGEL DİYOTLARIN HAZIRLANMASI VE ELEKTRİK İLE DİELEKTRİK ÖZELLİKLERİNİN FREKANS VE VOLTAJA BAĞLI İNCELENMESİ, Doktora, Ö.SEVGİLİ(Öğrenci), 2020

ALTINDAL Ş., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Yüksek Lisans, S.KOÇYİĞİT(Öğrenci), 2017

ALTINDAL Ş., USLU İ., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Yüksek Lisans, S.KOÇYİĞİT(Öğrenci), 2017

ALTINDAL Ş., Polimer arayüzey tabakalı ve tabakasız schottky engel diyotların elektriksel karakteristiklerinin karşılaştırılması, Doktora, Ç.BİLKAN(Öğrenci), 2016

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ALTINDAL Ş., Au/Ca₃Co₄Ga_{0,001}Ox/n-Si yapılarında doğru ve ters beslem akım-voltaj (I-V) karakteristiklerinin 80-340 K sıcaklık aralığında incelenmesi, Doktora, E.MARIL(Öğrenci), 2015

ALTINDAL Ş., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Yüksek Lisans, A.AYTİMUR(Öğrenci), 2015

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ALTINDAL Ş., Au/(%1 Grafen Katkılı)-Ca_{1.9}Pr_{0.1}Co₄Ox/N-Si Schottky Engel Diyotların Hazırlanması Ve Elektrik ile Dielektrik Özelliklerinin Sıcaklık Ve Frekansa Bağlı incelenmesi, Doktora, H.Gökçen(Öğrenci), 2015

ALTINDAL Ş., Au/ZnO/n-GaAs (MIS) Schottky engel diyotların (SBDs) elektriksel karakteristiklerinin frekans ve voltaja bağlı incelenmesi, Yüksek Lisans, B.AKIN(Öğrenci), 2015

ALTINDAL Ş., USLU İ., Grafen, bor ve nadir toprak elementleriyle katkılanmış poliviniliden florür nanokompozit piezo malzemelerin üretimi ve karakterizasyonu, Yüksek Lisans, Y.BADALI(Öğrenci), 2015

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ALTINDAL Ş., Metal-polimer-yarıiletken (MPS) yapıların elektrik ve dielektrik özelliklerinin geniş frekans aralığında

incelenmesi, Doktora, A.KAYA(Öğrenci), 2013

ALTINDAL Ş., Perilensiz ve perilenli Al/p-Si schottky engel diyotların elektriksel özelliklerinin oda sıcaklığında karşılaştırılması, Yüksek Lisans, Ç.BİLKAN(Öğrenci), 2013

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ALTINDAL Ş., (Ni/Au)/Al_{0.22}Ga_{0.78}N/AlN/GaN çoklu-yapıların elektriksel karakteristiklerinin admitans spektroskopisi metoduyla incelenmesi, Doktora, Y.ŞAFAK(Öğrenci), 2012

ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS)schottky engel diyodun elektriksel özelliklerinin sıcaklık ve radyasyona bağlı incelenmesi, Doktora, İ.TAŞÇIOĞLU(Öğrenci), 2012

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO₂/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve potansiyele bağlı incelenmesi, Doktora, Z.SÖNMEZ(Öğrenci), 2012

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ALTINDAL Ş., Au/SiO₂/n-Si (MIS) yapının elektrik ve dielektrik karakteristiklerinin sıcaklığa bağlı incelenmesi, Yüksek Lisans, A.GÜL(Öğrenci), 2011

ALTINDAL Ş., Al / Rhodamine - 101 / n-GaAs Schottky Engel diyotlarının hazırlanması ve iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, Ö.VURAL(Öğrenci), 2011

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ALTINDAL Ş., Au/(Bi-katkılı) polivinil alkol/n-si schottky engel diyotlarının elektriksel özelliklerinin sıcaklığa ve aydınlatma şiddetine bağlı incelenmesi, Yüksek Lisans, H.GÖKÇEN(Öğrenci), 2011

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ALTINDAL Ş., Al/SiO₂/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağlı incelenmesi, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., Al/SiO₂/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağlı incelenmesi, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağlı incelenmesi, Doktora, H.USLU(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.4}N/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.4}N/GaN heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., SiO₂/p-Si (MIS) YAPILARIN ELEKTRİK KARAKTERİSTİKLERİNİN FREKANS BAĞLI İNCELENMESİ, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa_{0.4}N/GaN HETEROYAPILARIN ELEKTRİKSEL KARAKTERİSTİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağlı incelenmesi, Doktora, H.USLU(Öğrenci), 2010

ALTINDAL Ş., Au/SrTiO₃/n-Si (MFS) Schottky diyotların elektriksel parametrelerinin I-V, C-V ve DLTS metodu ile incelenmesi, Yüksek Lisans, U.AYDEMİR(Öğrenci), 2009

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ALTINDAL Ş., Yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin sıcaklığa bağlı incelenmesi, Doktora, H.KANBUR(Öğrenci), 2008

ALTINDAL Ş., Au/SiO₂/n-GaAs (MOY) YAPILARIN ELEKTRİK VE DİELEKTRİK KARAKTERİSTİKLERİNİN FREKANS VE SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, M.GÖKÇEN(Öğrenci), 2008

ALTINDAL Ş., Al/ SiO₂/p-Si (MYY) YAPILARIN AKIM-İLETİM MEKANİZMASI VE ELEKTRİKSEL ÖZELLİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, Doktora, D.Esra(Öğrenci), 2008

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ALTINDAL Ş., MIS yapıların frekans ve radyasyona bağlı temel elektriksel parametreleri, Yüksek Lisans, B.TATAROĞLU(Öğrenci), 2006

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ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Schottky diyotlarının sıcaklığa bağlı temel parametreleri, Yüksek Lisans, E.MARIL(Öğrenci), 2005

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ALTINDAL Ş., MOS yapılarında temel fiziksel parametrelerin frekans ve radyasyon miktarına bağlı incelenmesi, Doktora, A.TATAROĞLU(Öğrenci), 2004

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- CXLVIII. **Investigation of negative dielectric constant in Au/1 % graphene (GP) doped-Ca_{1.9}Pr_{0.1}Co₄O_x/n-Si structures at forward biases using impedance spectroscopy analysis**

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- CLI. **A compare of electrical characteristics in Al/p-Si (MS) and Al/C₂₀H₁₂/p-Si (MPS) type diodes using current-voltage (I-V) and capacitance-voltage (C-V) measurements**

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- CLIV. **On the analysis of the leakage current in Au/Ca₃Co₄Ga_{0.001}O_x/n-Si structure in the temperature range of 80-340 K**

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- CLV. **Current-conduction mechanism in Au/n-4H-SiC Schottky barrier diodes**

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- CCXLII. **Temperature dependent dielectric properties of Schottky diodes with organic interfacial layer**

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Yildiz D. E., Altındal Ş.

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- CCLXXX. **MBE-growth and characterization of In_xGa_{1-x}As/GaAs (x=0.15) superlattice**

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- CCXCVII. **Effects of gamma-ray irradiation on the C-V and G/omega-V characteristics of Al/SiO₂/p-Si (MIS) structures**
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Afandiyeva I. M., Doekme İ., Altındal Ş., Abdullayeva L. K., Askerov S. G.
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Schottky diodes

Yildiz D. E., Altindal Ş.

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Parlaktuerk F., Altindal Ş., TATAROĞLU A., PARLAK M., Agasiev A.

MICROELECTRONIC ENGINEERING, cilt.85, sa.1, ss.81-88, 2008 (SCI-Expanded)

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- CII. On the temperature and voltage dependence of electrical and dielectric properties of the Au Bi₃Ti₄O₁₂ n Si MFS structure in the temperature range of 120 380 K**

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